

# Image Sensors and Spectrometers

John Gilmore, MSEE

Hamamatsu Corporation

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## Agenda

- Spectrometer Introduction
- UV Visible Image Sensors and Spectrometers
- NIR Spectrometers and InGaAs Image Sensor
- Quest for the "Perfect" Spectrometer
- New and Exciting μ-Spectrometers
- Summary



# **Design of Mini-Spectrometer**



# **Fundamental Building Blocks for Spectrometers**

## **MOEMS** Business Promotion

Semiconductor Technology
Packaging Technology
Optical knowledge
IC and ASIC Technology
FPGA and Software

# MOEMS

- M: Micro
- O: Opto
- E : Electro
- M : Mechanical
- S : System

# MOEMS Technology in Hamamatsu

#### MEMS technologies

Fine processing is used to enhance the functions of optical devices.

- Etching
- Nanoimprint
- Resist spray coating
- Bonding
- Through-hole electrode



## **MOEMS for Spectroscopy**



#### **Quartz Grating Wafer**



Narrow pitch and High aspect



#### Nanoimprinted Blazed grating





# **Example in Grating Spectral Orders**

- Multiple emission orders.
- Optical characteristics depend on grating design and fabrication.
  - ✓ Wavelength coverage
  - ✓ Optical resolution
  - ✓ Stray Light
  - ✓ Efficiency



# MOEMS & Image Sensor Technologies

#### **MOEMS technology**

Gratings for mini-spectrometers (TG/TM series) use a transmission type (made of quartz) fabricated by a HAMAMATSU holographic process.





spectrometer

#### **Image sensor technology**

# The detector that is the heart of the mini-spectrometer is a

HAMAMATSU image sensor.

# **Mini-spectrometer**



# **Market Challenges**

- Spectrometers
  - ✓ Demands for high precision, scientific instrument.
    - Linearity, stray light, wavelength and repeatability.
  - ✓ Moving the instrument to the sample, portability.
  - ✓ Broad wavelength coverage, UV MID IR.
  - ✓ Flat response, consistent Signal to Noise ratio.
  - ✓ High speed operation, electronic shutter with gating capability.
  - ✓ UV hardness, reliability and lifetime.



# **Spectrometers for Spectroscopy Applications**

- High sensitivity
- Rectangular active area
- Low noise, for low light applications
- Large saturation charge, wide dynamic range.
- Optical resolution.
- Stray light performance.



Wavelength (nm)

Example of NIR Spectrometer Stray Light

# **Image Sensor Operating Principle**





# **Consumer and Scientific image sensors**

Consumer image sensors

Digital camera, Mobile phone's camera

- > small pixel size, narrow dynamic range
- > high sensitivity in visible
- > low price and mass production efficiency
- Scientific image sensors

Analytical and measuring equipment, Industrial camera

- > larger pixel size, wider dynamic range
- > high sensitivity from UV to NIR
- > high accuracy and good linearity

## CCD / CMOS image sensors



# Market Demand ~ High Sensitivity (QE X Gain)

Front-illuminated type

Back-thinned type





## Visible - NIR Sensitivity Enhanced CCD



#### High VUV sensitivity CCD



# Market Demand ~ Reliability and Lifetime

High VUV sensitivity and reduced sensitivity deterioration by UV irradiation





# Why are CCD's low light champions? Three reasons - #1 Amplifier Noise





# <u>**Reason #2 - CCD Vertical Line Binning Operation**</u>

(1) Signal flow

Summing in the analog domain, before pixel readout, reduces total noise.

(FDA)



# **CCD Device Structure**

- Full Frame Transfer (FFT-CCD).
- Readout on the order of mSec (1-10mSec).





# **<u>CCD Line Binning Timing Chart</u>**

 Readout time determines spectrometers minimum exposure time.



## Reason #3 – High QE and high conversion gain.

### **Market Demand High-speed electronic shutter**



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## **CCD** with different charge transfer

	Interline CCD	Resistive gate CCD Back thinned type	Binning readout Back thinned type
	TUTUTUT	THERE THE THE THE THE THE THE THE THE THE TH	Ţ₽₽₽₽₽₽₽₽₽
Product	S15351(New)	S15254(New)	S703x, S10420,S11071
Charge transfer	Active area	Voltage low Voltage high	Potential Transfer direction
Feature	General application	High sensitivity E-shutter function	High sensitivity Wide dynamic range

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#### **High-speed electronic shutter**

- Basic concept
- Long pixel height
- Back illuminated type linear CCD
- > High speed e-shutter function
- Specification
- Pixel pitch 14um
- > Pixel height S15254:200um, S15257:2500um
- Shutter speed S15254: < 1us , S15257: 50us</p>
- > Readout Speed 5MHz(Typ), 10MHz(Max)
- > Full Well Capacity 200ke-
- > Dynamic range 6660
- Low image lag
- Application
- > LIBS
- Gating operation





#### Spectral response (without window)\*<sup>21</sup>





#### **Market Demand Spectrometers with Flat Response**





#### **Solutions for Spectrometer Saturation**

#### Application

Spectrometer

#### •Features

- Anti-blooming (saturation control)
- Horizontal pixels: 2048
- Vertical pixels :128, 256, 512
- Low noise type :S1014x-01
- High speed type : S1324x
- Large full well : 500ke-

(3 times larger than conventional)



Wavelength (nm)

## **Solutions for Saturation Control and Flat Response**

## Application

Spectrometer

## Benefits

- Readout bright portions of the spectrum, while allowing weaker signal to accumulate longer.
- Saturation Charge ~ 180pC

#### Equivalent circuit



CMOS image sensor with variable integration capabilities

## **Suppressed fringe of spectral sensitivity**

Suppressed the fringe of spectral sensitivity curve over a wide wavelength range.



# **CMOS ~ Difference between PPS and APS**

#### **Active Pixel Sensor**

The APS is a method with the amplifier in each pixel.



#### **Passive Pixel Sensor**

The PPS is a method with only one amplifier at the end of video line.



## **Buried Photodiode technologies**



# **Higher sensitivity CMOS-APS with Buried PD**

- Features
  - Higher pixel in size(14x200um)
  - Higher sensitivity with buried PD
  - APS (Active Pixel Sensor)
  - Sensitivity 1300V/lx s
    - (8 times higher than conventional type)
  - Electronic shutter
- Application
  - Spectrometer
- Specification
  - 14um x 200um, 2048ch



## **CCD vs CMOS Image sensors**

	CCD	CMOS
Output (pixel)	charge	voltage
Amplifier	1-amp for multi pixels	1-amp for single pixel
Output(chip)	voltage (analog)	digital/analog
Charge transfer	from pixel to pixel	inside of pixel
Fabrication	specialized process for CCD	common LSI process
Input bias	multiple, high, voltage clocking	single, low,DC
Onchip circuit	Very difficult	possible
External circuit	complicated	simple



# **CCD vs CMOS image sensors**

#### CCD image sensor

- Signal charges are transferred in Si.
- Charges are converted to voltage "after" transferring.

#### CMOS image sensor

-Signal voltage is transferred in the metal.

- Charges are converted to voltage "before" transferring.





# UV – Visible (SWIR) Summary (190nm-1100nm)

- Spectrometers & Image Sensors
  - ✓ CCD based solutions excellent for low light levels.
  - CMOS-APS spectrometers, portable implementations for middle range.
  - CMOS-PDA spectrometers with variable integration time and huge dynamic range. Absorption applications with bright light, detecting small changes.

# NIR Image Sensors and Spectrometers (900-2500nm)



намамат

## **NIR Spectrometers**

C14486GA		
Remote And		
950 to 1700 (NIR)	Incidence Slit Focusing Lens Image Senso	
5.0 typ		
InGaAs	Optical fiber	
256	Collimating Lens Transmission Gratings	
80 x 60 x 12		
88		
	C14486GA         NEW         NEW         S0 to 1700         (NIR)         5.0 typ         InGaAs         256         80 x 60 x 12         88	


## **Compound Semiconductors for IR sensors**



## InGaAs

#### Good candidate to replace



# InGaAs image sensor spectral response



## For wide wavelength spectrometer 2 types InGaAs in 1PKG



## InGaAs Hybrid Linear image sensors

- Single video line 512ch
- High speed readout 5MHz max.
- 255ch(0.95-1.7um)&255ch(1.4-2.2um)

## (Back Illuminated Type)



# <u>Market Demand ~ "Perfect" Spectrometer</u>

## Stray Light Corrections

Simple spectral stray light correction method for array spectroradiometers

Yuqin Zong, Steven W. Brown, B. Carol Johnson, Keith R. Lykke, and Yoshi Ohno







# <u>Market Demand ~ "Perfect" Spectrometer</u>

Linearity Corrections

Article Improving Optical Measurements: Non-Linearity Compensation of Compact Charge-Coupled Device (CCD) Spectrometers Münevver Nehir <sup>1</sup>, Carsten Frank <sup>2,3</sup>, Steffen Aßmann <sup>3,4</sup> and Eric P. Achterberg <sup>1,\*</sup>



**Figure 7.** Pixel intensities (counts) versus integration time (ms). A single line represents data from one pixel. Data from 200 representative pixels (equally spaced between 400–800 nm) are shown. All data lines appear to be linear up to 50,000 counts and then deviate strongly from the ideal line.





# MOEMS Technologies New Technology creates new solutions ..... Micro-Spectrometers

# New development for NIR Mini-Spectrometer

Grating design has some limitation to make smaller and cheaper

- > Have to use a very expensive Image sensor
- > Very difficult to get higher resolution in limited so pace
- Difficult to design wide wavelength spectrometer

How to realize small and cheap NIR spectrometers ? Not Grating type but

"Interference Spectrometer using <u>Actuator</u>"

# Focusing on Portable Implementations

➢Mini-spectrometer SMD series (640 to 1050 nm)

>MEMS-FPI spectrum sensor (e.g.,1550 to 1850 nm)

≻Compact FTIR engine (1100 to 2500 nm)







## Hamamatsu Contributions to Industry

# Industry Agriculture Recycle Infrastructure - incoming test - Process control Image: Control for the process analysis Image: Control for the process analysis Image: Control for the process analysis - Wet process analysis Image: Control for the process analysis Image: Control for the process analysis Image: Control for the process analysis - How the process analysis Image: Control for the process analysis Image: Control for the process analysis Image: Control for the process analysis - How the process analysis Image: Control for the process analysis Image: Control for the process analysis Image: Control for the process analysis - How the process analysis Image: Control for the process analysis Image: Control for the process analysis Image: Control for the process analysis - How the process analysis Image: Control for the process analysis Image: Control for the process analysis Image: Control for the process analysis - How the process analysis Image: Control for the process analysis Image: Control for the process analysis Image: Control for the process analysis - How the process analysis Image: Control for the process analysis Image: Control for the process analysis Image: Control for the process analysis - How the process analysis Image: Control for the p







Features:

> Integrated MEMS chip and beam splitter prism

Manufactured with less optical adjustment



## • SNR improvement by NEW FTIR Engine (vs old model)

	New FTIR Engine C15511-01	Old MEMS-FTIR C12606-02	<ul> <li>Expanded spectral range up to 2500 nm</li> </ul>	
	* Mirror size : 3mm dia.	* SU2000 1.0kV 7.9mmgk30 LM(U)	- Improved sensitivity about 100 times (*2) 10 <sup>-6</sup> (Halogen lamp: 2800K, optical fiber core: 600 µm	
Spectral range	1100 to 2500 nm	1150 to 2050 nm		
SNR *1	10,000 : 1 (40dB)	1,000 : 1 (30dB)		
Resolution	25cm-1 = 5.7 nm (1533nm)	29cm-1 = 6.8nm (1533nm)	Light integration of the second secon	
Size	57 x 49 x 76 mm (212,000mm <sup>3</sup> )	100 x 75 x 27 mm (202,500mm <sup>3</sup> )	$10^{-12}$ $10^{-13}$ $10^{-13}$ $1.0$ $1.3$ $1.6$ $1.9$ $2.2$	

\*1 : The SNR values are on conditions optimized to each type.

\*2: The graph on the right shows the sensitivity improvement by 100 times, whose measurements are on conditions optimized to C15511-01. (i.e. too weak light for C12606-02)

Wavelength (nm)

РНОТОМ

NA: 0.2)

MM

2.5



# <u>Compact FTIR engine - design concept</u>





# Optical system of FTIR engine (cross-sectional view)

Two interferometers separated by a dichroic mirror

Passive alignments are applied with positioning pins





# <u>Compact FTIR engine – Test sample –</u>





## **Compact FTIR engine** –Evaluation result –



# Compact FTIR engine application : degradation of mortal



**Compact FTIR engine – application : alcoholic beverage** 





## Comparison with desktop FTIR instrument

HAMAMATSU

The absorption peaks of glucose, sucrose and fructose can be found by the FTIR engine C15511-01, which is correspondent with the data by the desktop FTIR instrument



## <u>MEMS-FPI Spectral sensor –Lineup</u>







### MEMS-FPI Spectral sensor –Tunable filter –

#### A tunable filter that adjust transmission wavelength by the applied voltage



# **Structure of MEMS-FPI**



## **Feature**

- > Small PKG : TO-5
- Super lightweight : 1g
- Hermetic PKG
- Single InGaAs-PD included
- Thermistor included
- Band pass filter included



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# MEMS-FPI spectral sensor \_Characteristics -



# **MEMS FPI : Wavelength transmission response**

## FPI Type : C14273 (1750~2150nm)





# MEMS-FPI Spectral sensor –Evaluation kit–



## MEMS-FPI spectrum module features

UNDER DEVELOPMENT



## Compact • Thin

- Size : 74×32×16mm
- MEMS-FPI spectrum sensor built-in
  - > 3 types C15712, C15713, C15714 are available
- USB2.0 bus-power operation
- Transmission wavelength compensation
  - Transmission wavelength shift by ambient temperature (Max.0.9nm/°C) can be compensated by circuit
- High speed measurement
  - <1 sec/scan is possible (at 1 nm step between 300 or 400nm wavelength range)</p>

Built-in lamp

- Reflection measurement is available
- Transmission measurement is also available with Lamp OFF
- Software
  - > In addition to evaluation software, DLL can be provided soon
- Option
  - > SMA fiber attachment (option) is available.

It will be released on Spring, 2020



Operating temperature : -5~+50°C Spectral resolution (FWHM) C15712 : 18nm C15713 : 20nm C15714 : 22nm



## MEMS-FPI spectrum module application example







Material identification by spectrum differences





# **FPI & FTIR Summary Table**

Item	MEMS-FPI spectral sensor	Compact FTIR
Method	Fabry-Perot interferometer Tunable filter	Michelson interferometer FTIR
Wavelength length region	1.35-1.65µm, 1.55-1.85µm, 1.75-2.15µm	1.15-2.5µm
Wavelength resolution	18nm@1.65µm, 20nm@1.85µm, 22nm@2.15µm	11nm@1.5µm
Detector	InGaAs PIN PD single element	InGaAs PIN PD
Light incident method	Window	Optical fiber (SMA)
Product form	Sensor component or module Module – Temperature Compensation Component – User calibrate	Module



# Market Demand – Move the instrument to the sample



Pocket Spectrometer for Color Analysis

## **Components for Mini& Micro-Spectrometers**



Optical slit on the same CMOS image sub.



Color Filter on CMOS image sensor



#### Master Lens for Replication



#### Blazed Grating by Nanoimprint



jU

## 2<sup>nd</sup> Gen. Micro Spectrometer



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# **Strategy for much smaller Spectrometer**



намама **Optical design Micro spectrometer SMD-type** Input slit Input slit Mirror **CMOS CMOS Down sizing** \*\*\*\*\* Mirror **Concave Grating** Window glass light **CMOS Image Concave Grating** sensor



# **Components of MOEMS Spectrometer**





# <u>Micro-spectrometer SMD type-C14384MA-</u>



## Feature

- Grating type
- Ultra compact, light weigt
- Thin type, Side looker
- Wavelength : 640 ~ 1050nm
- High sensitivity, high speed
- Flexible cable connection
- Target market
- food, agriculture, environment monitor

#### The smallest size as a grating type spectrometer !



## **Construction / Optical characteristic**

Item	C14384MA	Unit
Spectral response range	640-1050	nm
Number of pixels	256	pixels
Clock pulse frequency	5	MHz
Slit size	15×300	μm
NA	0.22	-
Spectral resolution (FWHM)	20(Max.)	nm
Wavelength temperature dependence	±0.1	nm/°C
Wavelength reproducibility	±0.5	nm
Spectral stray light	-23	dB


### Line-up of spectrometers using MOEMS grating





## Grating type compact spectrometer series

## MS series

weight:9g C10988MA(340~750nm) C11708MA(640~1050nm)

#### Micro series

weight: 5g C12666MA(340~780nm) C12880MA(340~850nm)

### SMD series

weight : <0.3g C14384MA(640~1050nm)



# **MOEMS Spectrometers**



# **Summary**

- Optical MEMS (MOEMS) devices to enrich sensor information remarkably, which will make "real-time, on-site measurements in various fields" possible.

- Downsizing, cost reduction of the devices
- $\rightarrow$  to be utilized in more and more handy products
- $\rightarrow$  to be utilized in more and more production lines
- $\rightarrow$  to be utilized in our daily lives more and more





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3	Understanding Spectrometer	2	9-Jun-20	11-Jun-20
1 Weeks Break				
4	Specialty Products – Introduction to Light Sources & X-Ray	2	23-Jun-20	25-Jun-20
5	Introduction to Image Sensors	2	30-Jun-20	02-Jul-20
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